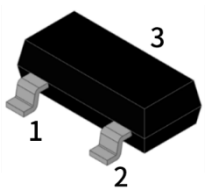
SS8050LST1

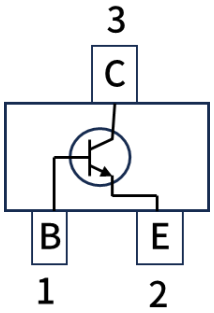
General Purpose Transistors NPN

1. FEATURES

- The material of product compliance with RoHS requirements and Halogen Free.
- High Stability and High Reliability.
- Complementary to SS8550LST1(PNP).
- High current capacity in compact package. IC =1.5 A.



SOT23 (TO-236)



2. Mechanical Data

- SOT-23 Small Outline Plastic Package.
- Tin plated leads, solderable per J-STD-002 and JESD22-B102.
- Marking: Y1

3. ORDERING INFORMATION

Device	Min Pack	Inner Box	Outer Carton	Reel
SS8050LST1	3000	45000	180000	7 inch

4. MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Limit	Unit
Collector-Emitter Voltage	VCEO	25	V
Collector-Base Voltage	VCBO	40	V
Emitter-Base Voltage	VEBO	5	V
Collector Current--Continuous	Ic	1.5	A
Collector Power Dissipation	Pc	300	mW

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Limit	Unit
Operation Junction and Storage Temperature Range	TSTG	-55~150	°C
Thermal Resistance Junction to Ambient	RΘJA	417	°C/W

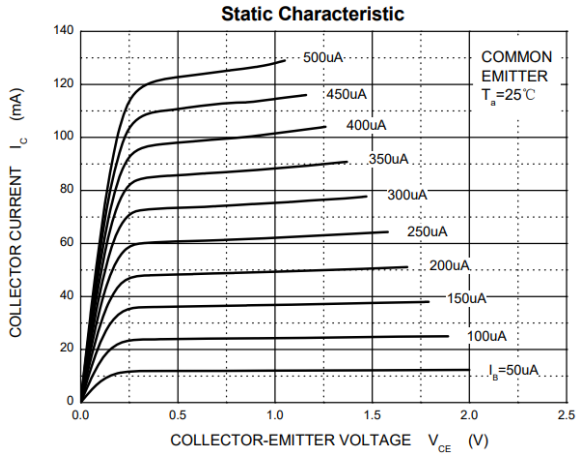
6. ELECTRICAL CHARACTERISTICS (Ta= 25°C unless otherwise specified)

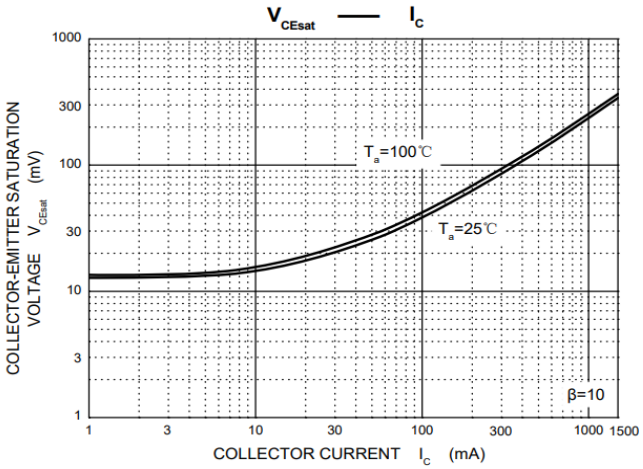
Parameter	Symbol	Condition	Min	Max	Unit
Collector-Emitter Breakdown Voltage	V(BR)CEO	IC = 0.1mA, IB = 0	25		V
Collector-Base Breakdown Voltage	V(BR)CBO	IC = 0.1mA, IE = 0	40		V
Emitter-Base Breakdown Voltage	V(BR)EBO	IE = 0.1mA, IC = 0	5		V
Collector-Emitter Cutoff Current	ICEO	VCE = 20 V, IE=0		100	nA
Collector Cutoff Current	ICBO	VCB= 40 V, IB=0		100	nA
Emitter cut-off current	IEBO	VEB= 5V, IC=0		100	nA
DC current gain	hFE(1)	IC = 100mA, VCE = 1 V	120	400	
DC current gain	hFE(2)	IC = 800 mA, VCE = 1 V	40		
Collector-Emitter Saturation voltage	VCE(sat)	IC = 800mA, IB = 80mA		0.5	V
Base-Emitter Saturation Voltage	VBE(sat)	IC = 800mA, IB = 80 mA		1.2	V
Transition frequency	fT	VCE=10V, IC= 50mA, f=30MHz	100		MHz

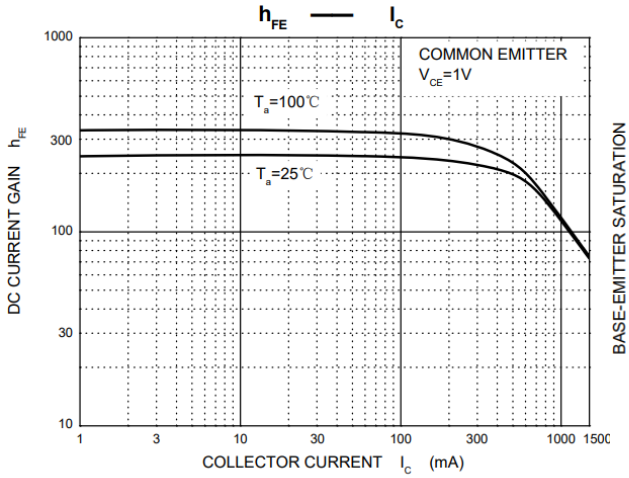
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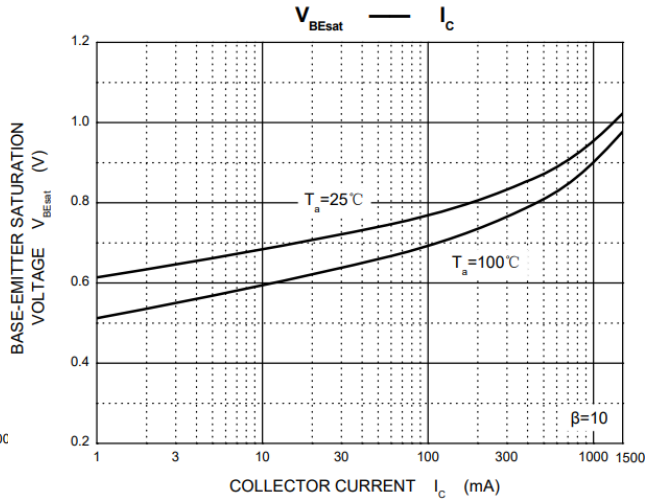
RANK	L	H	J
RANGE	120-200	200-350	300-400

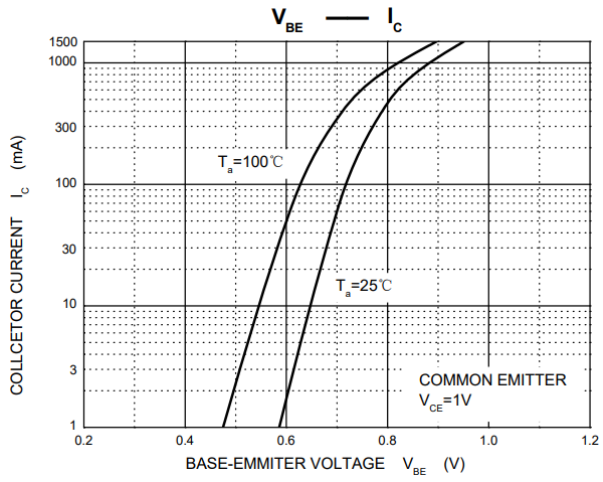
8. ELECTRICAL CHARACTERISTICS CURVES

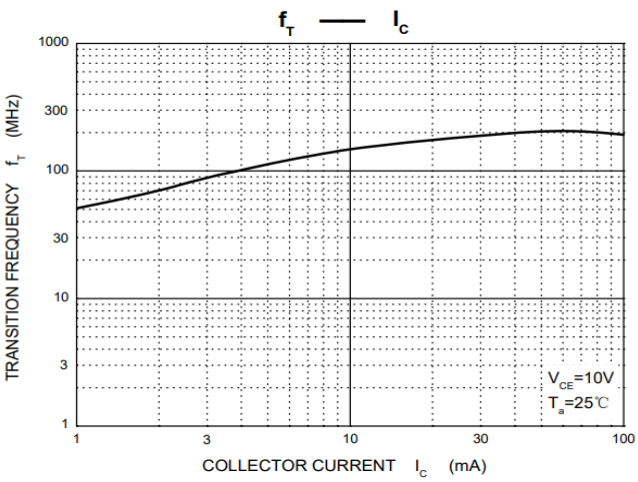




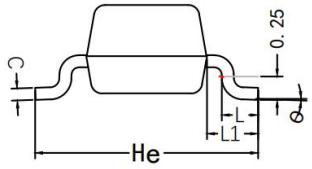


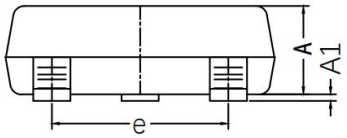


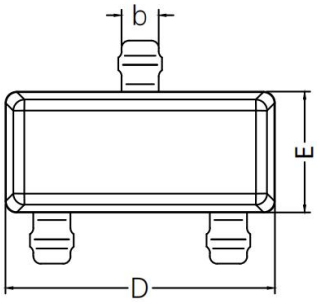




9. OUTLINE AND DIMENSIONS

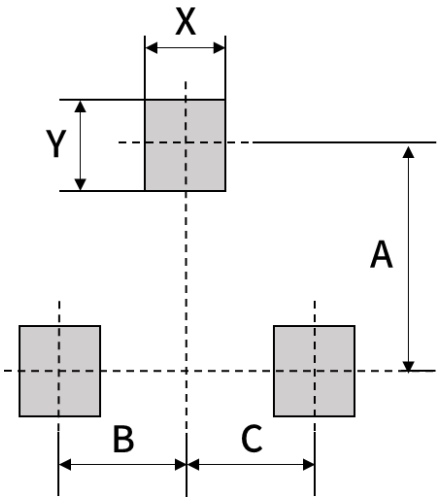






DIM	MIN	NOR	MAX
A	0.85	0.95	1.05
A1	0.01	0.06	0.10
b	0.36	0.44	0.52
c	0.09	0.13	0.18
D	2.80	2.90	3.10
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.40	0.50
L1	0.35	0.50	0.65
He	2.10	2.35	2.50
θ	0°	-	10°
All Dimensions in mm			

10. SUGGESTED PAD LAYOUT



SOT23		
DIM	mm	inch
A	2.00	0.079
B	0.95	0.037
C	0.95	0.037
X	0.80	0.031
Y	0.90	0.035

11. DISCLAIMER

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